

Amendments to the Claims:

Listing of Claims:

5 Claims 1-241 (canceled)

242. (currently amended) A ~~chip packaging~~ method for fabricating a chip package comprising:

10 joining a die and a substrate, said die having a top surface at horizontal level,
 wherein said die and said substrate are under said horizontal level;

after said joining said die and said substrate, forming a patterned circuit layer over
 said horizontal level, said patterned circuit layer extending across an edge of said die;

15 after said joining said die and said substrate, forming ~~depositing~~ a passive device
 over said horizontal level, substrate, wherein said passive device is entirely ~~has a portion~~
 not directly over said die; and

 separating said substrate into multiple portions.

243. (currently amended) A ~~chip packaging~~ method for fabricating a chip package comprising:

20 joining a die and a substrate, said die having a top surface at horizontal level,
 wherein said die and said substrate are under said horizontal level;

 after said joining said die and said substrate, forming ~~depositing~~ a passive device
 over said horizontal level, said passive device having a first connection point connected to
 said die;

25 after said forming ~~depositing~~ said passive device, forming ~~depositing~~ a metal
 bump over said horizontal level, wherein said metal bump is connected to a second
 connection point of said passive device; and

 separating said substrate into multiple portions.

244. (currently amended) A ~~chip packaging method~~ for fabricating a chip package comprising:

- 5 providing a first die having a first top surface at a horizontal level;
 providing a second die having a second top surface at said horizontal level;
 ~~forming~~ ~~depositing~~ a passive device over said horizontal level, wherein said
passive device is entirely has a portion not directly over said first and second dies; ~~and~~
 after said forming said passive device over said horizontal level, forming an
10 insulating layer on said passive device; and
 ~~forming~~ ~~depositing~~ a patterned circuit layer ~~metal trace~~ over said horizontal level,
wherein said patterned circuit layer ~~metal trace~~ extends across an edge of said first ~~or~~
~~second~~ die.

245. (currently amended) The method of claim 242, wherein said substrate comprises a
15 metal substrate.

246. (previously presented) The method of claim 242 further comprising joining a film
and said substrate, an opening in said film exposing said substrate, followed by said
joining said die and said substrate exposed by said opening.

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247. (currently amended) The method of claim 246, wherein forming said opening in said
film comprising a punching process.

248. (currently amended) The method of claim 246, wherein said film comprises a metal
25 layer.

Claim 249 (canceled)

250. (currently amended) The method of claim ~~242, 249~~, wherein said ~~forming depositing~~ said patterned circuit layer comprises an electroplating process.

251. (currently amended) The method of claim ~~242, 249~~, wherein said ~~forming depositing~~ said patterned circuit layer comprises a sputtering process.

252. (currently amended) The method of claim 242, wherein said ~~forming depositing~~ said passive device comprises an electroplating process.

253. (withdrawn - currently amended) The method of claim 242, wherein said ~~forming depositing~~ said passive device comprises a sputtering process.

254. (currently amended) The method of claim 242, after said joining said die and said substrate, further comprising ~~forming depositing~~ a solder bump over said horizontal level, ~~substrate~~, followed by said separating said substrate.

255. (withdrawn - currently amended) The method of claim 242, after said joining said die and said substrate, further comprising ~~forming depositing~~ a gold bump over said horizontal level, ~~substrate~~, followed by said separating said substrate.

256. (currently amended) The method of claim 242, wherein said forming said patterned circuit layer and said forming depositing said passive device are ~~is~~ followed by said separating said substrate.

257. (currently amended) The method of claim 243, wherein said substrate comprises a metal substrate.

258. (previously presented) The method of claim 243 further comprising joining a film and said substrate, an opening in said film exposing said substrate, followed by said joining said die and said substrate exposed by said opening.

5 259. (currently amended) The method of claim 258, wherein forming said opening in said film comprising a punching process.

260. (currently amended) The method of claim 258, wherein said film comprises a metal layer.

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261. (currently amended) The method of claim 243, after said joining said die and said substrate, further comprising forming ~~depositing~~ a patterned circuit layer over said horizontal level, ~~die and over said substrate~~, said patterned circuit layer extending across an edge of said die, followed by said separating said substrate.

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262. (currently amended) The method of claim 261, wherein said forming ~~depositing~~ said patterned circuit layer comprises an electroplating process.

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263. (currently amended) The method of claim 261, wherein said forming ~~depositing~~ said patterned circuit layer comprises a sputtering process.

264. (currently amended) The method of claim 243, wherein said forming ~~depositing~~ said passive device comprises an electroplating process.

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265. (withdrawn - currently amended) The method of claim 243, wherein said forming ~~depositing~~ said passive device comprises a sputtering process.

266. (currently amended) The method of claim 243, wherein said ~~forming depositing~~ said metal bump comprises ~~forming depositing~~ a solder bump over said horizontal level, wherein said solder bump is connected to said second connection point.

- 5 267. (withdrawn - currently amended) The method of claim 243, wherein said ~~forming depositing~~ said metal bump comprises ~~forming depositing~~ a gold bump over said horizontal level, wherein said gold bump is connected to said second connection point.

268. (currently amended) The method of claim 243, wherein said ~~forming depositing~~ said
10 metal bump is followed by said separating said substrate.

269. (currently amended) The method of claim 244, wherein said ~~forming depositing~~ said patterned circuit layer ~~metal trace~~ comprises an electroplating process.

- 15 270. (currently amended) The method of claim 244, wherein said ~~forming depositing~~ said patterned circuit layer ~~metal trace~~ comprises a sputtering process.

271. (currently amended) The method of claim 244, wherein said ~~forming depositing~~ said
20 passive device comprises an electroplating process.

272. (withdrawn - currently amended) The method of claim 244, wherein said ~~forming depositing~~ said passive device comprises a sputtering process.

273. (currently amended) The method of claim 244, after said ~~forming depositing~~ said
25 insulating layer ~~passive device~~ and said ~~forming depositing~~ said patterned circuit layer, ~~metal trace~~, further comprising ~~forming depositing~~ a solder bump over said horizontal level.

274. (withdrawn - currently amended) The method of claim 244, after said forming
~~depositing~~ said insulating layer ~~passive device~~ and said forming ~~depositing~~ said patterned
circuit layer, ~~metal trace~~, further comprising forming ~~depositing~~ a gold bump over said
horizontal level.

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